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| <p>Substitute for Form 1449 A & B/PTO</p> <p>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</p> <p>(use as many sheets as necessary)</p> | | | | <i>Complete if Known</i> | |
| | | | | Application Number | 10/510,916 |
| | | | | Confirmation Number | 7320 |
| | | | | Filing Date | October 12, 2004 |
| | | | | First Named Inventor | Shinichi ISHIBASHI |
| | | | | Art Unit | 2812 |
| | | | | Examiner Name | Not yet assigned |
| Sheet | 1 | of | 1 | Attorney Docket Number | Q84137 |

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| Examiner Initials ^a | Cite No. ¹ | Document Number | | Publication Date MM-DD-YYYY | Name of Patentee or Applicant of Cited Document |
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| | | Number | Kind Code ² (if known) | | |
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| | | Country Code ³ | Number ⁴ | Kind Code ⁵ (if known) | | | |
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NON PATENT LITERATURE DOCUMENTS

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| Examiner Initials ^a | Cite No. ¹ | Include name of the author (in CAPITAL LETTERS), title of the article (where appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published. | Translation ^d |
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| Examiner Signature | | Date Considered |
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